

Silicon Carbide (SiC) Schottky Diode – EliteSiC, 20 A, 1200 V, D1, TO-247-2L

FFSH20120A-F155

Description

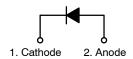
Silicon Carbide (SiC) Schottky Diodes use a completely new technology that provides superior switching performance and higher reliability compared to Silicon. No reverse recovery current, temperature independent switching characteristics, and excellent thermal performance sets Silicon Carbide as the next generation of power semiconductor. System benefits include highest efficiency, faster operating frequency, increased power density, reduced EMI, and reduced system size and cost.

Features

- Max Junction Temperature 175°C
- Avalanche Rated 200 mJ
- High Surge Current Capacity
- Positive Temperature Coefficient
- Ease of Paralleling
- No Reverse Recovery/No Forward Recovery
- This Device is Pb-Free, Halogen Free/BFR Free and RoHS Compliant

Applications

- General Purpose
- SMPS, Solar Inverter, UPS
- Power Switching Circuits

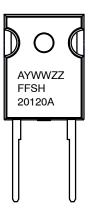


Schottky Diode



TO-247-2LD CASE 340DC

MARKING DIAGRAM



A YWW ZZ FFSH20120A

1

= Assembly Plant Code = Date Code (Year & Week)

= Lot Code

= Specific Device Code

ORDERING INFORMATION

See detailed ordering and shipping information on page 2 of this data sheet.

FFSH20120A-F155

ABSOLUTE MAXIMUM RATINGS ($T_C = 25$ °C unless otherwise noted)

Symbol	Parameter	Value	Unit	
V_{RRM}	Peak Repetitive Reverse Voltage		1200	V
E _{AS}	Single Pulse Avalanche Energy (Note 1)		200	mJ
lF	Continuous Rectified Forward Current @ T _C < 153°C		20	А
	Continuous Rectified Forward Current @ T _C <	Continuous Rectified Forward Current @ T _C < 135°C		А
I _{F,Max}	Non-Repetitive Peak Forward Surge Current	T _C = 25°C, 10 μs	1190	А
		T _C = 150°C, 10 μs	990	А
I _{F,SM}	Non-Repetitive Forward Surge Current	Half-Sine Pulse, t _p = 8.3 ms	135	Α
I _{F,RM}	Repetitive Forward Surge Current	Half-Sine Pulse, t _p = 8.3 ms	74	Α
P _{TOT}	Power Dissipation	T _C = 25°C	273	W
		T _C = 150°C	46	W
T _J , T _{STG}	Operating and Storage Temperature Range		-55 to +175	°C

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

THERMAL CHARACTERISTICS

Symbol	Parameter	Value	Unit
$R_{ heta JC}$	Thermal Resistance, Junction to Case, Max	0.55	°C/W

ELECTRICAL CHARACTERISTICS (T_C = 25°C unless otherwise noted)

Symbol	Parameter	Test Condition	Min	Тур	Max	Unit
V _F	Forward Voltage	I _F = 20 A, T _C = 25°C	-	1.45	1.75	V
		I _F = 20 A, T _C = 125°C	=	1.7	2.0	
		I _F = 20 A, T _C = 175°C	=	2.0	2.4	
I _R	Reverse Current	V _R = 1200 V, T _C = 25°C	=	=	200	μΑ
		V _R = 1200 V, T _C = 125°C	=	=	300	
		V _R = 1200 V, T _C = 175°C	=	=	400	
Q_{C}	Total Capacitive Charge	V = 800 V	=	120	=	nC
С	Total Capacitance	V _R = 1 V, f = 100 kHz	=	1220	=	pF
		V _R = 400 V, f = 100 kHz	-	111	-	
		V _R = 800 V, f = 100 kHz	-	88	-	

Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.

ORDERING INFORMATION

Part Number	Top Marking	Package	Packing Method	Quantity
FFSH20120A-F155	FFSH20120A	TO-247-2LD	Tube	30 Units

^{1.} E_{AS} of 200 mJ is based on starting $T_J = 25^{\circ}C$, L = 0.5 mH, $I_{AS} = 29$ A, V = 150 V.

FFSH20120A-F155

TYPICAL CHARACTERISTICS

(T_J = 25°C UNLESS OTHERWISE NOTED)

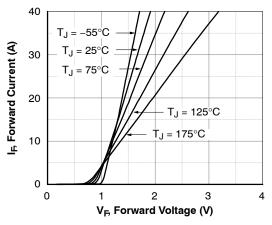


Figure 1. Forward Characteristics

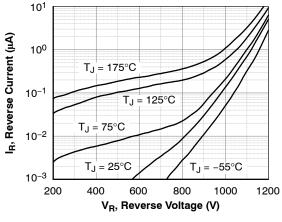


Figure 2. Reverse Characteristics

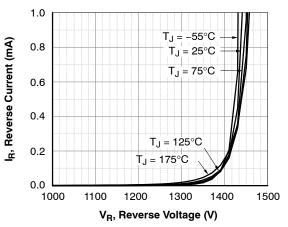


Figure 3. Reverse Characteristics

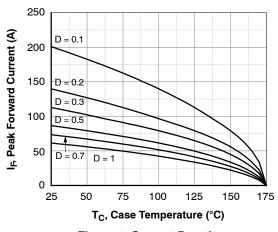


Figure 4. Current Derating

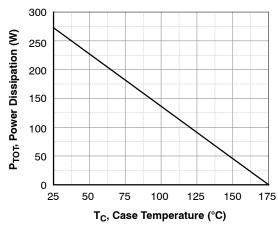


Figure 5. Power Derating

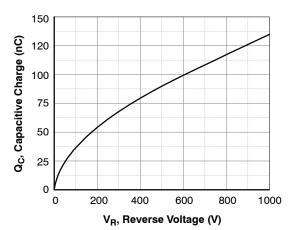


Figure 6. Capacitive Charge vs. Reverse Voltage

FFSH20120A-F155

TYPICAL CHARACTERISTICS (CONTINUED)

(T_J = 25°C UNLESS OTHERWISE NOTED)

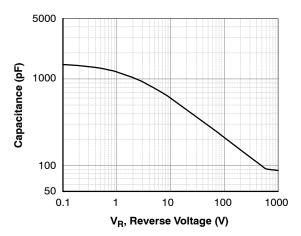


Figure 7. Capacitance vs. Reverse Voltage

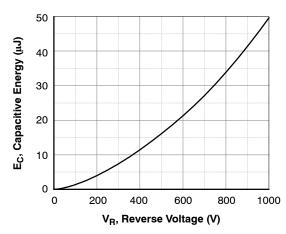


Figure 8. Capacitance Stored Energy

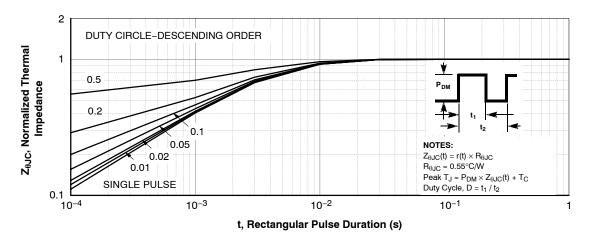


Figure 9. Junction-to-Case Transient Thermal Response Curve

TEST CIRCUIT AND WAVEFORMS

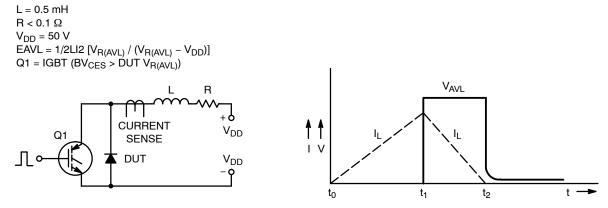
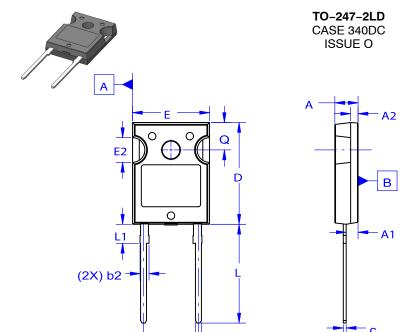
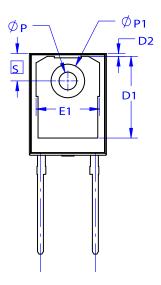


Figure 10. Unclamped Inductive Switching Test Circuit & Waveform



DATE 09 JUL 2020



NOTES:

A. DIMENSIONS ARE EXCLUSIVE OF BURRS, MOLD FLASH AND TIE BAR PROTRUSIONS.

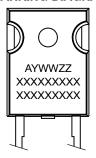
(2X) b

0.25 M B A M

- B. ALL DIMENSIONS ARE IN MILLIMETERS.
- C. DIMENSION AND TOLERANCE AS PER ASME Y14.5-2009.
- D. DIMENSION A1 TO BE MEASURED IN THE REGION DEFINED BY L1.
- E. LEAD FINISH IS UNCONTROLLED IN THE REGION DEFINED BY L1.

DIM	MILLIMITERS				
DIM	MIN	NOM	MAX		
Α	4.58	4.70	4.82		
A 1	2.20	2.40	2.60		
A2	1.40	1.50	1.60		
b	1.17	1.26	1.35		
b2	1.60	1.72	1.84		
С	0.51	0.61	0.71		
D	20.32	20.57	20.82		
D1	13.08	~	~		
D2	0.51	0.93	1.35		
Е	15.37	15.62	15.87		
E1	12.81	~	~		
E2	4.96	5.08	5.20		
е	~	11.12	~		
L	19.75	20.00	20.25		
L1	3.69	3.81	3.93		
<u> </u>	3.51	3.58	3.65		
Ø P 1	6.60	6.80	7.00		
Q	5.34	5.46	5.58		
S	5.34	5.46	5.58		

GENERIC MARKING DIAGRAM*



XXXXX = Specific Device Code

A = Assembly Location Y = Year

WW = Work Week
ZZ = Assembly Lot Code

*This information is generic. Please refer to device data sheet for actual part marking. Pb—Free indicator, "G" or microdot "■", may or may not be present. Some products may not follow the Generic Marking.

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